

PSMN3R0-60PS

N-channel 60 V 3.0 m Ω standard level MOSFET Rev. 02 — 28 October 2010

Product data sheet

1. **Product profile**

1.1 General description

Standard level N-channel MOSFET in a TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$		-	-	60	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	306	W
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>		-	2.4	3	mΩ
Dynamic ch	naracteristics						
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 80 A; V_{DS} = 12 V; see <u>Figure 13</u> ; see <u>Figure 14</u>		-	28	-	nC
Avalanche	ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 60 V; R_{GS} = 50 Ω; unclamped		-	-	800	mJ

^[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		G (EA)
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R0-60PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

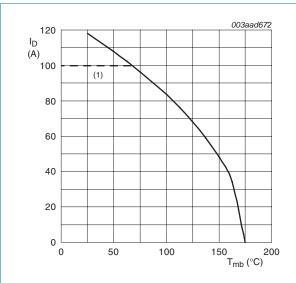
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>		-	83.4	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3		-	824	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	306	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain of	diode					
Is	source current	T _{mb} = 25 °C	<u>[1]</u>	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	824	Α
Avalanche rug	gedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C; } I_D = 100 \text{ A; } V_{SUD} \le 60 \text{ V; } R_{GS} = 50 \Omega; \text{ unclamped}$		-	800	mJ

[1] Continuous current is limited by package.

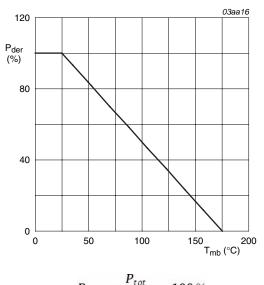
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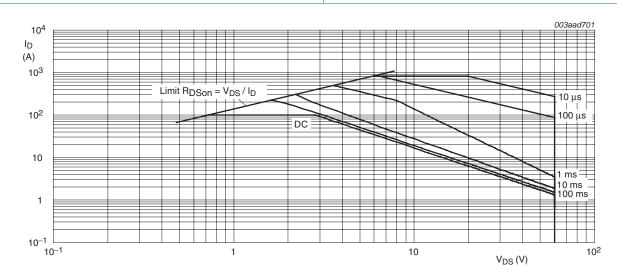
 $V_{\it GS} \geq$ 10 V(1) Capped at 100 A due to package

Fig 1. Continuous drain current as a function of mounting base temperature.



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



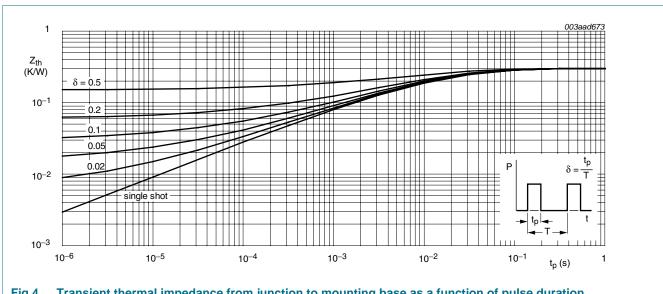
 T_{mb} = 25 °C; I_{DM} is a single pulse; Capped at 100 A due to package

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.49	K/W



Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics	0	N.5.	T		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 V; T_j = -55 ^{\circ}\text{C}$	54	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 8</u> ; see <u>Figure 9</u>	2	3	4	V
V_{GSth}	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see <u>Figure 9</u>	1	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 9	-	-	4.6	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 10	-	-	7.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 11; see Figure 12	-	2.4	3	mΩ
R _G	gate resistance	f = 1 MHz	-	1.1	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 80 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13; see Figure 14	-	130	-	nC
Q_{GS}	gate-source charge	$I_D = 80 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 13	-	43	-	nC
Q_{GD}	gate-drain charge	$I_D = 80 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14	-	28	-	nC
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 15}}{\text{see Figure 16}};$	-	8079	-	pF
C _{oss}	output capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 15}{\text{ Composition}}$	-	971	-	pF
C _{rss}	reverse transfer capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 15}}{\text{see Figure 16}};$	-	492	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 10 \text{ V};$	-	31	-	ns
t _r	rise time	$R_{G(ext)} = 1.5 \Omega$	-	26	-	ns
t _{d(off)}	turn-off delay time		-	77	-	ns
t _f	fall time		-	22	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 17	-	0.88	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	54	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}$	-	97	-	nC

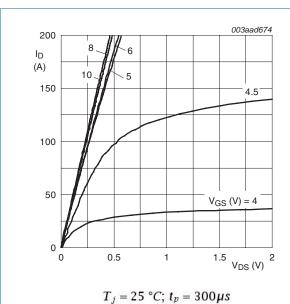


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

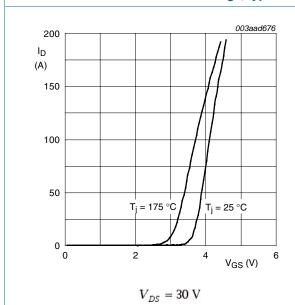


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

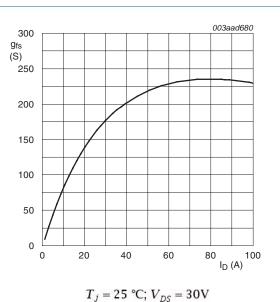


Fig 6. Forward transconductance as a function of

drain current; typical values

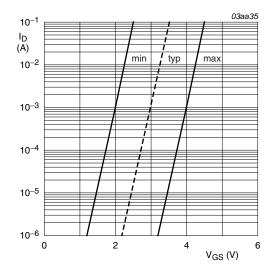
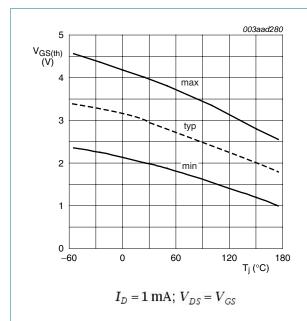


Fig 8. Sub-threshold drain current as a function of gate-source voltage

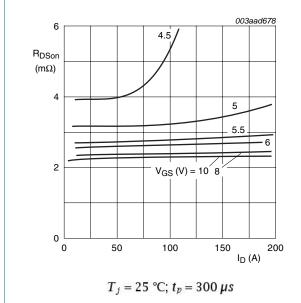
 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$



a $\frac{3}{a}$ $\frac{003aad773}{2}$ $\frac{2}{0-60}$ $0 \qquad 60 \qquad 120 \qquad T_{j} (^{\circ}C) \qquad 180$ $a = \frac{R_{DSon}}{R_{DSon(25 ^{\circ}C)}}$

Fig 9. Gate-source threshold voltage as a function of junction temperature

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



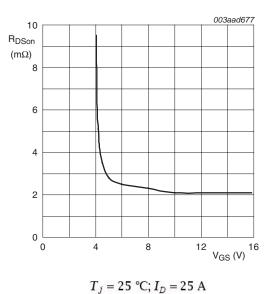


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



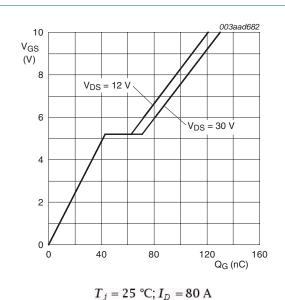


Fig 13. Gate-source voltage as a function of gate charge; typical values

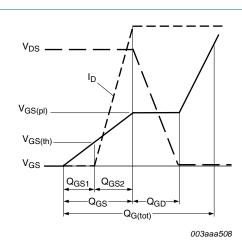


Fig 14. Gate charge waveform definitions

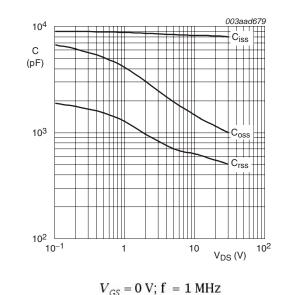


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

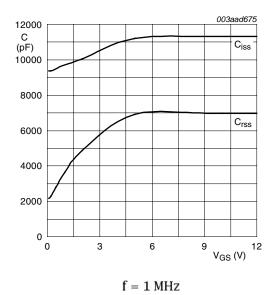


Fig 16. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

values

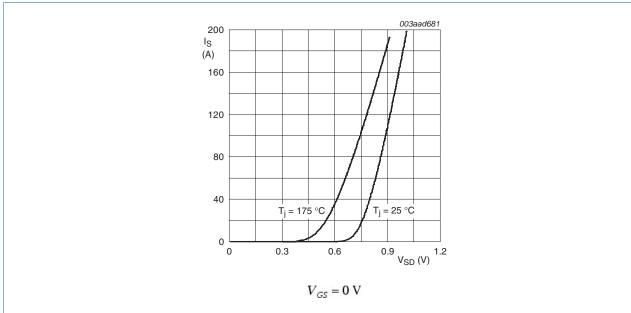
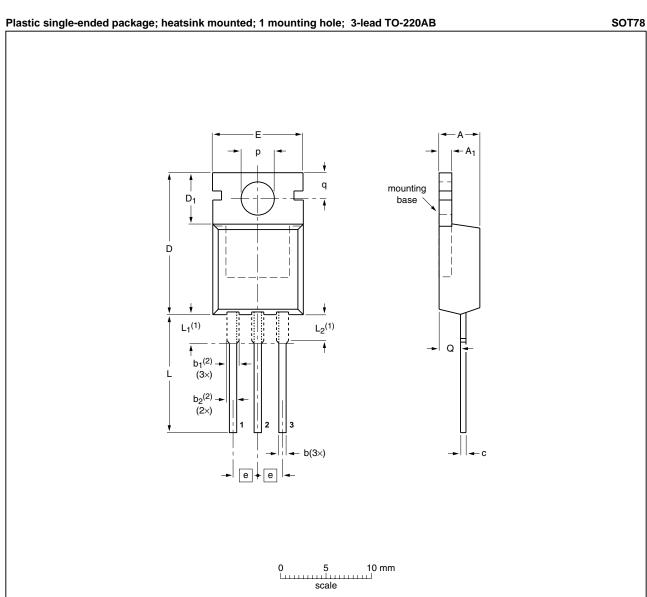


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline



DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ (2)	b ₂ (2)	С	D	D ₁	E	е	L	L ₁ (1)	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE	UTLINE REFERENCES		REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE		
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13		

Fig 18. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R0-60PS v.2	20101028	Product data sheet	-	PSMN3R0-60PS v.1
Modifications:	 Various changes 	to content.		
PSMN3R0-60PS v.1	20091123	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Nexperia

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11. Contents

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